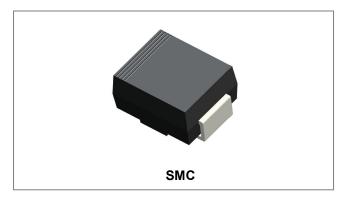






30BQ040 SCHOTTKY RECTIFIER



Features

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	40	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =118°C, rectangular wave form	3.0	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse, T _C =25°C	132	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 3 A, Pulse, T _J = 25 °C	0.50	0.53	V
		@ 6 A, Pulse, T _J = 25 °C	0.65	0.68	V
	V_{F2}	@ 3 A, Pulse, T _J = 125 °C	0.40	0.43	V
		@ 6 A, Pulse, T _J = 125°C	0.55	0.57	V
Reverse Current*	I _{R1}	@V _R = Rated V _R , Pulse, T _J = 25 °C	0.01	0.5	mA
	I _{R2}	@V _R = Rated V _R , Pulse, T _J = 100 °C	7	30	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	130	230	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body	3.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 μs, duty cycle < 2%

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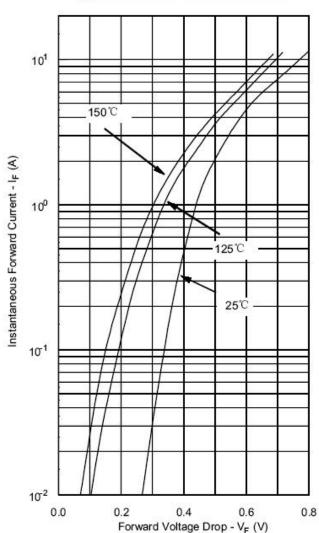


Thermal-Mechanical Specifications:

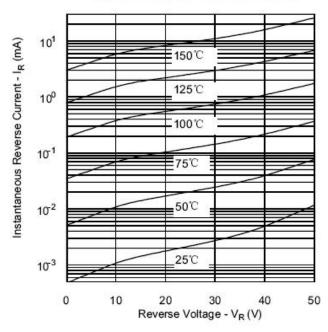
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +125	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Lead	$R_{ heta JL}$	-	12	°C/W
Typical Thermal Resistance Junction to Case	R _{θJA}	DC operation	46	°C/W
Approximate Weight	wt	-	0.21	g
Case Style	SMC			

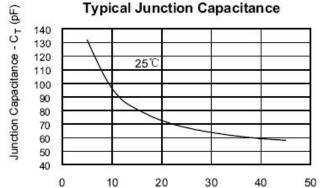
Ratings and Characteristics Curves

Typical Forward Characteristics



Typical Reverse Characteristics





Reverse Voltage - VR (V)

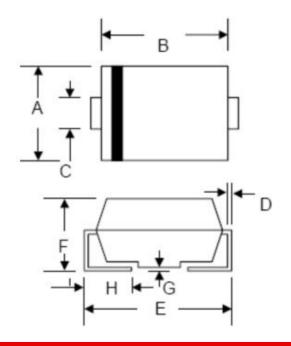
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Mechanical Dimensions SMC



CYMPOL	Millin	neters	Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	5.59	6.22	0.220	0.245	
В	6.60	7.11	0.260	0.280	
С	2.75	3.25	0.108	0.128	
D	0.152	0.305	0.006	0.012	
E	7.75	8.25	0.305	0.325	
F	2.00	2.95	0.079	0.116	
G	0.051	0.203	0.002	0.008	
Н	0.76	1.60	0.030	0.063	

Ordering Information

Device	Package	Shipping	
30BQ040	SMC (Pb-Free)	3000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

Where XXXXX is YYWWL



 SC3F
 = Part Name

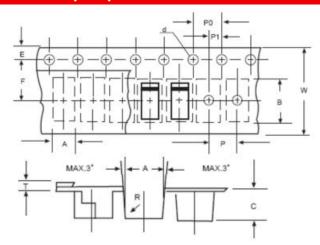
 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification SMC



SYMBOL	Millin	neters
	Min.	Max.
Α	5.90	6.10
В	8.20	8.40
C	2.40	2.60
d	1.40	1.60
E	1.40	1.60
F	7.60	7.70
Р	7.90	8.10
P0	3.90	4.10
P1	3.90	4.10
Т	-	0.600
W	15.80	16.20

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